

**Patent Abstracts of Japan**

PUBLICATION NUMBER : 2001044498  
 PUBLICATION DATE : 16-02-01

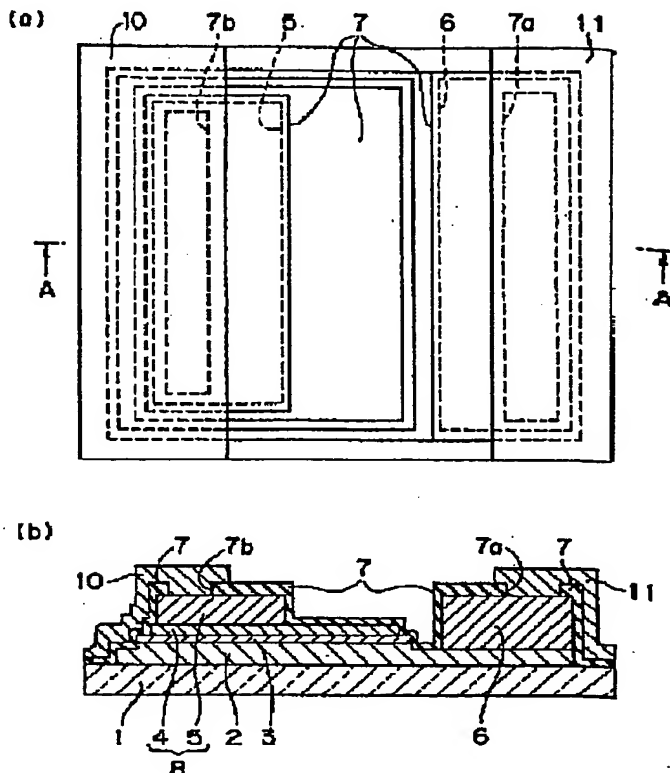
APPLICATION DATE : 28-07-99  
 APPLICATION NUMBER : 11213606

APPLICANT : NICHIA CHEM IND LTD;

INVENTOR : KOMAKI TOSHIO;

INT.CL. : H01L 33/00

TITLE : NITRIDE SEMICONDUCTOR  
 LIGHT-EMITTING DEVICE



**ABSTRACT :** PROBLEM TO BE SOLVED: To provide a nitride semiconductor light-emitting device that can effectively prevent short-circuiting between electrodes in manufacturing (flip-chip bonding).

**SOLUTION:** In a nitride semiconductor light-emitting device that is equipped with an n-type nitride semiconductor layer formed on a transparent substrate, an n electrode and a p-type nitride semiconductor layer 3 separated from each other on an n-type nitride semiconductor layer 2, a p electrode provided at one part of the p-type nitride semiconductor layer 3, and an insulation protecting film provided so that each semiconductor layer and each electrode are covered except the opening part of each upper surface of n and p electrodes, a first conductor 10 for conducting electricity to the p electrode is formed on the insulation protection film outside the opening part on the p electrode, and a second conductor 11 for conducting electricity to the n electrode is formed on the insulation protection film outside the opening part on the n electrode.

COPYRIGHT: (C)2001,JPO